

IN THE CLAIMS

1-19. (Canceled)

20. (Original): A method of making an electrostatic discharge semiconductor device on a semiconductor substrate having a first conductivity type and a first doping concentration, comprising:

implanting into the substrate first, second, and third well regions having second conductivity types that are opposite in polarity to said first conductivity type;

implanting a fourth well region of the first conductivity type adjacent to said substrate and adjacent to said first well region; and

forming an insulated terminal across said second and said third well regions.

21. (Original): The method of claim 20, further comprising implanting a fifth well region into said substrate having the first conductivity type and a second doping concentration.

22. (Original): The method of claim 20, wherein implanting said fourth well comprises doping the fourth well region with a second doping concentration that is greater than the first doping concentration.

23. (Original): The method of claim 20, further comprising forming an insulated terminal above said first well region.

24. (Original): The method of claim 20, wherein said fourth well region comprises a halo region adjacent to said first well region that reduces a breakdown voltage between the first well region to the substrate.

25. (Original): The method of claim 20, wherein the fourth well region comprises forming a lightly doped drain adjacent to said first well region that reduces a breakdown voltage between said first well region to said substrate.

26. (Original): The method of claim 20, wherein said fourth well region is adjacent to said second well region that reduces a breakdown voltage between said first well region to said substrate.